

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1176	438/123.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 10:21
S2	981	S1 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 11:13
S3	28	438/901.ccls. and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:26
S4	54	361/271.ccls. and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 14:16
S5	115679	capacitor and semiconductor and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:31
S6	3110	S5 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:39
S7	655	S6 and (wet or chemical) adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:40
S8	7	S7 and PETEOS	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:32
S9	619	S5 and sacrificial and supporting	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:57
S10	148	S9 and (wet or chemical) adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:36
S11	2139	S5 and sacrificial and (support\$3 or spacer)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 13:57
S12	504	S11 and (wet or chemical) adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 14:16

S13	206	438/399.ccls. and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/25 15:07
S14	25	S13 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/28 08:53
S15	14	"L10" and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:53
S16	206	438/399.ccls. and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/28 08:54
S17	25	S16 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/28 08:54
S18	1660	semiconductor and sacrificial and supporting and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/02/28 08:55
S19	957	semiconductor and sacrificial and supporting and electrode and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:56
S20	616	semiconductor and sacrificial and supporting and electrode and dielectric and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:57
S21	190	S20 and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:59
S22	2108	PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_"))	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 12:07

S23	1730	S22 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 12:08
S24	399	S23 and capacitor	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 12:08
S25	142	S23 and capacitor.ab.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 13:26
S26	2108	PTEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_"))	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:26
S27	1730	S26 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 15:34
S28	142	S27 and capacitor.ab.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 13:26
S29	22	S28 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 14:05
S30	559	PTEOS	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 14:05
S31	454	S30 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 14:06

S32	2	S28 and sacrifice	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 14:07
S33	45	S31 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 14:07
S34	77	@ad<="20021002" and capacitor and sacrificial and (PETEOS or HDP) and (HSQ or BPSG or PSG)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 15:46
S35	2	@ad<="20021002" and (PETEOS or HDP) and (HSQ or BPSG or PSG) and etch near bias	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/02/28 15:47
S36	115737	capacitor and semiconductor and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:36
S37	619	S36 and sacrificial and supporting	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:36
S38	148	S37 and (wet or chemical) adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:36
S39	1	S38 and PETEOS	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:50
S40	534	438/738.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 10:51
S41	493	438/738.ccls. and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 11:00
S42	7	438/738.ccls. and @ad<="20021002" and PETEOS	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 11:44

S43	1672	(438/738.ccls. and @ad<="20021002") and PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_"))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 11:45
S44	15	(438/738.ccls. and @ad<="20021002") and (PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_")))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:42
S45	27	(438/738.ccls. and @ad<="20021002") and (PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_")) or high adj density adj plasma adj oxide or HDP adj oxide)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:06
S46	16	S45 and (hydrogen adj silsesquioxane or HSQ or borophosphosilicate adj glass or BPSG or phosphosilicate or PSG)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:08
S47	707	@ad<="20021002" and (PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_")) and (hydrogen adj silsesquioxane or HSQ or borophosphosilicate adj glass or BPSG or phosphosilicate or PSG)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:47
S48	0	S47 and wet adj etc	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:44

S49	118	S47 and wet adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:44
S50	261	@ad<="20021002" and (PETEOS or ((plasma adj enhanced) and (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_")) same(hydrogen adj silsesquioxane or HSQ or borophosphosilicate adj glass or BPSG or phosphosilicate or PSG)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 13:48
S51	46	S50 and wet adj etch	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 14:31
S52	585	438/386.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 14:32
S53	485	S52 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 14:34
S54	3	S53 and PETEOS	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 14:42
S55	2	S53 and plasma adj enhanced adj TEOS	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 14:42
S56	40	S53 and ((high adj density adj plasma adj oxide) or HDP)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/03/01 16:22
S57	2	"5162248".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/01 16:31
S58	2	"5392189".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/01 16:36

S59	2	"5786259".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/01 16:43
S60	2	"5858829".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/01 16:47
S61	2	"5902124".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/01 16:58
S62	2	"5972769".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 15:40
S63	2333	(crown or cylindrical) near capacitor	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 15:41
S64	136	S63 and sacrificial	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 15:41
S65	110	S64 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 15:42
S66	8	S65 and support\$3 adj layer	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 16:13
S67	2	"5336917".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/02 16:13

S68	619	PETEOS or ((plasma adj enhanced) adj (tetraethylorthosilicate or tetraethyl adj orthosilicate or tetraethyl-orthosilicate or tetraethoxy adj silane or tetraethoxysilane or tetra-ethoxy adj silane or Si adj "OC.sub.2 H. sub.5_"))	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:29
S69	496	S68 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:29
S70	7	S69 and cylindrical adj capacitor	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:40
S71	207	S69 and (HSQ or BPSG or PSG)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:41
S72	188	S68 same(HSQ or BPSG or PSG)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:41
S73	137	S72 and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 08:42
S74	36	S73 and wet adj etch	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:43
S75	15	("5153813" "5155657" "5753948" "5817553" "5843822" "5903430" "5998260" "6027968" "6030879" "6064085" "6100129" "6114201" "6127220" "6133600" "6271084").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/03 09:55
S76	0	((("5153813" "5155657" "5753948" "5817553" "5843822" "5903430" "5998260" "6027968" "6030879" "6064085" "6100129" "6114201" "6127220" "6133600" "6271084").PN.) and PETEOS	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/03 09:56

S77	9	((("5153813" "5155657" "5753948" "5817553" "5843822" "5903430" "5998260" "6027968" "6030879" "6064085" "6100129" "6114201" "6127220" "6133600" "6271084").PN.) and BPSG	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/03 10:10
S78	1	(HF adj vapor adj etch) same (HF adj wet adj etch)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:14
S79	0	(HF adj dry adj etch) same (HF adj wet adj etch)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:14
S80	1	(HF adj vapor adj etch) near (HF adj wet adj etch)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:15
S81	2	"5310626".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 14:28
S82	599	capacitor and ((upper or top) adj electrode) same (contact adj plug) and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 14:32
S83	0	capacitor and ((upper or top) adj electrode) same (contact adj plug) same dielectri and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 14:32
S84	418	capacitor and ((upper or top) adj electrode) same (contact adj plug) same dielectric and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 14:33
S85	348	capacitor.ab. and ((upper or top) adj electrode) same (contact adj plug) same dielectric and @ad<="20021002"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:21
S86	2	"6399438".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:21

S87	124316	capacitor.ti.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/04 08:44
S88	2	"6399438".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/04 08:44